Quad 2-Input AND Gate

The MC74VHCT08A is an advanced high speed CMOS 2-input AND gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5 V CMOS level output swings.

The VHCT08A input structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. The output structures also provide protection when $V_{CC}=0$ V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed: $t_{PD} = 4.3 \text{ ns (Typ)}$ at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2 \mu A \text{ (Max)}$ at $T_A = 25 \text{°C}$
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model; > 2000 V, Machine Model; > 200 V
- Chip Complexity: 24 FETs or 6 Equivalent Gates
- Pb–Free Package May be Available.* The G–Suffix Denotes a Pb–Free Lead Finish

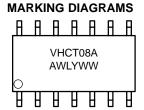


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SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



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VHCT08A



CASE 965

SOEIAJ-14
M SUFFIX

VHCT08A = Specific Device Code A = Assembly Location

WL = Wafer Lot Y = Year WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHCT08ADR2	SOIC-14	2500 / Tape & Reel
MC74VHCT08ADTR2	TSOP-14	2500 / Tape & Reel
MC74VHCT08ADTR2G	TSOP-14	2500 / Tape & Reel
MC74VHCT08AM	SOEIAJ- 14	50 Units / Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

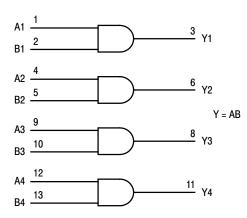


Figure 1. Logic Diagram

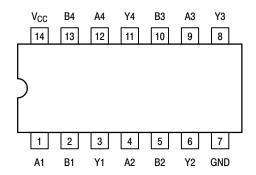


Figure 2. Pinout: 14-Lead Packages (Top View)

FUNCTION TABLE

Inp	uts	Output		
Α	В	Y		
L	L	L		
L	Н	L		
Н	L	L		
Н	Н	Н		

MAXIMUM RATINGS*

Symbol	Paramete	r	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{in}	DC Input Voltage		-0.5 to +7.0	V
V _{out}	DC Output Voltage		-0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current		-20	mA
I _{OK}	Output Diode Current		±20	mA
I _{out}	DC Output Current, per Pin		±25	mA
I _{CC}	DC Supply Current, V _{CC} and G	ND Pins	±50	mA
P _D	Power Dissipation in Still Air,	SOIC Packages† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature		-65 to +150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	4.5	5.5	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature	-40	+ 85	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	20	ns/V

DC ELECTRICAL CHARACTERISTICS

			V _{cc}	T _A = 25°C		T _A ≤	85°C	T _A ≤ '	125°C		
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		3.0 4.5 5.5	1.2 2.0 2.0			1.2 2.0 2.0		1.2 2.0 2.0		V
V _{IL}	Maximum Low-Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
V _{OH}	Minimum High-Level Output Voltage $V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V _{OL}	Maximum Low-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
Icc	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			2.0		20		40	μΑ
I _{CCT}	Quiescent Supply Current	Input: V _{IN} = 3.4 V	5.5			1.35		1.50		1.65	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5 V	0.0			0.5		5.0		10	μΑ

^{*} Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

[†]Derating - SOIC Packages: - 7 mW/°C from 65° to 125°C TSSOP Package: - 6.1 mW/°C from 65° to 125°C

AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0 \text{ns}$)

			1	Γ _A = 25°	С	T _A ≤	85°C	T _A ≤ '	125°C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Max	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A or B to Y	$V_{CC} = 3.0 \pm 0.3V$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		6.2 8.7	8.8 12.3		10.5 14.0		14.0 17.5	ns
		$V_{CC} = 5.0 \pm 0.5 V$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		4.3 5.8	5.9 7.9		7.0 9.0		9.0 11.0	
C _{in}	Maximum Input Capacitance			4	10		10		10	pF

		Typical @ 25°C, V _{CC} = 5.0V		ĺ
C_{PD}	Power Dissipation Capacitance (Note 1)	20	pF	l

^{1.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per gate). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.7

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$, $C_L = 50 \text{pF}$, $V_{CC} = 5.0 \text{ V}$)

		T _A = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

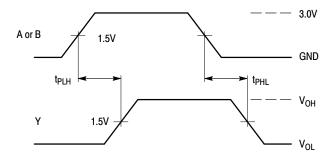
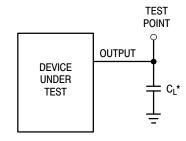


Figure 3. Switching Waveforms

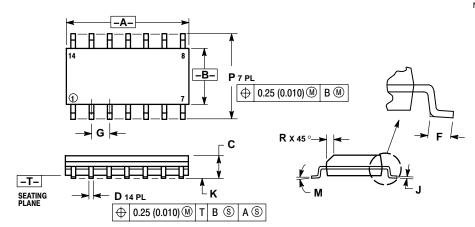


*Includes all probe and jig capacitance

Figure 4. Test Circuit

PACKAGE DIMENSIONS

SOIC-14 **D SUFFIX** CASE 751A-03 ISSUE F

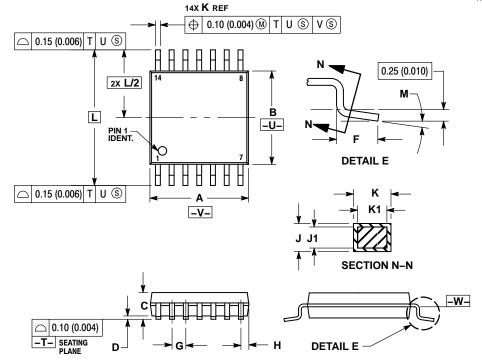


- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE
- MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE DAMBAR
- PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES		
DIM	MIN	MAX	MIN	MAX		
Α	8.55	8.75	0.337	0.344		
В	3.80	4.00	0.150	0.157		
С	1.35	1.75	0.054	0.068		
D	0.35	0.49	0.014	0.019		
F	0.40	1.25	0.016	0.049		
G	1.27	BSC	0.050	BSC		
J	0.19	0.25	0.008	0.009		
K	0.10	0.25	0.004	0.009		
M	0°	7°	0°	7°		
Р	5.80	6.20	0.228	0.244		
R	0.25	0.50	0.010	0.019		

TSSOP-14 **D SUFFIX** CASE 948G-01 ISSUE O



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI DIMENSIOI Y14.5M. 1982.
- CONTROLLING DIMENSION: MILLIMETER.
- B. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED
- FLASH OH GATE BUHRS SHALL NOT EXCEED
 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT
 EXCEED
- EXCEED
 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN
 EXCESS OF THE K DIMENSION AT MAXIMUM
 MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252 BSC	
M	0°	8°	0°	8°

PACKAGE DIMENSIONS

SOEIAJ-14 **M SUFFIX** CASE 965-01 **ISSUE O** Q_1 Ε ΗĘ **DETAIL P** е 0.13 (0.005) M 0.10 (0.004)

NOTES:

- 1. DIMENS... Y14.5M, 1982. DIMENSIONING AND TOLERANCING PER ANSI
 - CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE
- MOLD FLASH OR PROTRUSIONS AND ARE
 MEASURED AT THE PARTING LINE, MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- I. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050	BSC
HE	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z		1.42		0.056

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